

## List of reference symbols

10	Semiconductor substrate
11	Substrate passivation
12	Mask, preferably photolithographically patterned
12A	BPSG layer
12B	TEOS layer
13	Implanted doping in the substrate (high concentration)
14	Polysilicon (poly-Si)
15	Metal silicide e.g. W Si x or metal
16	Silicon nitride (SiN)
17	Sidewall oxide (SWOX)
17'	Thinned sidewall oxide (SWOX)
18	Implanted doping in the substrate (low concentration)
19	Gate stack side encapsulation (SiN or SiON)
TK	Storage capacitor
I	Implantation direction
$\alpha$	Implantation angle
GS1, GS2, GS3, GS4	Gate stack
X1	Vertical doping extent
X2	Horizontal distance between contact implant and gate contact opening
X3	Horizontal distance between gate stack sidewall and contact implant
d	Horizontal distance between gate contact hole opening and gate stack sidewall